

L Number	Hits	Search Text	DB	Time stamp
-	1	"5604059".PN.	USPAT	2002/10/21 14:40
-	1	430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$)	EPO; DERWENT; IBM_TDB	2002/10/21 16:19
-	146	430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$)	USPAT; US-PGPUB; JPO	2002/11/21 13:09
-	1	"6042998".PN.	USPAT	2002/10/21 18:09
-	1	"5989952".PN.	USPAT	2002/10/21 18:13
-	1	"5841143".PN.	USPAT	2002/10/21 18:15
-	4951	430/311-313,394.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 09:54
-	1481	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:23
-	698	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:55
-	541	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4) and ((line\$2 or parallel) same expos\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56
-	398	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4) and ((line\$2 or parallel) same expos\$3) and develop\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56
-	66	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4) and ((line\$2 or parallel) same expos\$3) and develop\$4 and (dynamic adj random adj access or DRAM)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:57
-	769	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56
-	602	((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5) and ((line\$2 or parallel) same expos\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56

438	(((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:57
74	(((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 11:52
331	(((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 11:55
62	(((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 13:35
4	((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/312.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 12:30
2	((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/394.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 12:31

-	3	(((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/313.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 13:11
-	3	(((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 13:11

-	57	<p>((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) not (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/312.ccls.) not (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/394.ccls.) not (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/313.ccls.) not (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls.)</p>	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	2002/12/04 09:57
-	5004	430/311-313,394.ccls.	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	2002/12/04 10:24
-	2009	430/312,394.ccls.	<p>USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	2002/12/04 10:27

-	324	430/312,394.cor.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/12/04 15:45
-	13	("4591540" "5286584" "5308741" "5340700" "5424154" "5532090" "5563012" "5620816" "5702868" "5804339" "5807649" "5851707" "5863677").PN.		2002/12/04 12:36
-	1685	430/312,394.ccls. not 430/312,394.cor.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/06 13:59
-	2995	430/311-313,394.ccls. not 430/312,394.ccls. not 430/312,394.cor.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/04 19:14
-	2	(("5103274") or ("5120671")).PN.	US-PGPUB USPAT;	2002/12/07 14:02
-	3	(("6184151") or ("5955244") or ("20010028422")).PN.	US-PGPUB USPAT; US-PGPUB	2002/12/10 14:44